

**Amendments to the Specification**

*In the Abstract, please amend as shown.*

Consistent with an example embodiment, a trench ~~A trench~~-FET has source regions (14) arranged above insulated gates (10)-in trenches (6). A body region ~~Body region~~ (20) of opposite conductivity type is arranged between the trenches (6) and a body ~~body~~-contact region (18) is arranged above the body region (20). Source contact metallisation (22) contacts the source (14) and body contact region (20). In this way a small cell pitch can be achieved.